L Number	Hits	Search Text	DB	Time stamp
1	1446	high-voltage NEAR circuit$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:06
2	531	(high-voltage NEAR circuit$1) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:06
3	256	((high-voltage NEAR circuit$1) and transistor) and ((input output) NEAR terminal$)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:07
4	239	(((high-voltage NEAR circuit$1) and transistor) and ((input output) NEAR terminal$)) and (source darin gate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:07
5	104	((((high-voltage NEAR circuit$1) and transistor) and ((input output) NEAR terminal$)) and (source darin gate)) and ((first second third) NEAR voltage)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:37
6	1137	330/253.ccls.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:37
7	175	330/253.ccls. and (high-voltage (high NEAR voltage))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:26
8	0	(330/253.ccls. and (high-voltage (high NEAR voltage))) and (sourece NEAR2 drain NEAR2 gate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:40
9	57	(330/253.ccls. and (high-voltage (high NEAR voltage))) and (source NEAR2 drain NEAR2 gate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:26
10	172	(330/253.ccls. and (high-voltage (high NEAR voltage))) and amplifier$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:09
11	142	((330/253.ccls. and (high-voltage (high NEAR voltage))) and amplifier$1) and terminal$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:58
12	142	(((330/253.ccls. and (high-voltage (high NEAR voltage))) and amplifier$1) and terminal$1) and (input output)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:58
13	142	((((330/253.ccls. and (high-voltage (high NEAR voltage))) and amplifier$1) and terminal$1) and (input output)) and voltage$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 12:59
14	2	(((((330/253.ccls. and (high-voltage (high NEAR voltage))) and amplifier$1) and terminal$1) and (input output)) and voltage$1) and (field ADJ transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:09
15	9	330/253.ccls. and (field ADJ transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:05
16	51	330/$.ccls. and (field ADJ transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:05

17	8645	257/$.ccls. and amplifier$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:16
18	86	(257/$.ccls. and amplifier$1) and (field ADJ transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:17
19	96	257/368.ccls. and amplifier$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:24
20	1	(257/368.ccls. and amplifier$1) and (field ADJ transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:17
21	90	(257/368.ccls. and amplifier$1) and transistor$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:17
22	88	(field ADJ transistor) same amplifier$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:25
23	357	(field ADJ transistor) and amplifier$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:25
24	137	((field ADJ transistor) and amplifier$1) and (high-voltage (high NEAR voltage))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:26
25	46	(((field ADJ transistor) and amplifier$1) and (high-voltage (high NEAR voltage))) and (source NEAR2 drain NEAR2 gate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/15 13:26